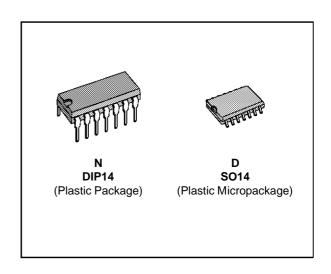


TS274C,I,M

HIGH SPEED QUAD CMOS OPERATIONAL AMPLIFIERS

- EXCELLENT PHASE MARGIN ON CAPACITIVE LOADS
- SYMETRICAL OUTPUT CURRENTS
- HIGH GAIN BANDWIDTH PRODUCT
- LOW OUTPUT DYNAMIC IMPEDANCE
- THE TRANSFER FUNCTION IS LINEAR
- PIN TO PIN COMPATIBLE WITH STANDARD QUAD OP-AMPs (TL084 -LM324)
- STABLE AND LOW OFFSET VOLTAGE
- THREE INPUT OFFSET VOLTAGE SELECTIONS



ORDER CODES

Part Number	Temperature	Package		
T art Number	Range	N	D	
TS274C/AC/BC	0°C, +70°C	•	•	
TS274I/AI/BI	-40°C, +125°C	•	•	
TS274M/AM/BM	-55°C, +125°C	•	•	

Example: TS274ACN

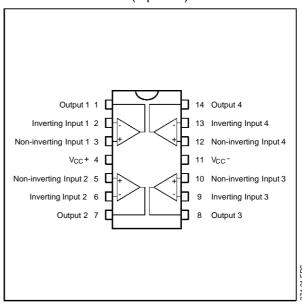
DESCRIPTION

The TS274 series are low cost, low power quad operational amplifiers designed to operate with single or dual supplies. These operational amplifiers use the SGS-THOMSON silicon gate LIN MOS process giving them an excellent consumption-speed ratio. These series are ideally suited for low consumption applications.

Three power consumptions are available allowing to have always the best consumption-speed ratio:

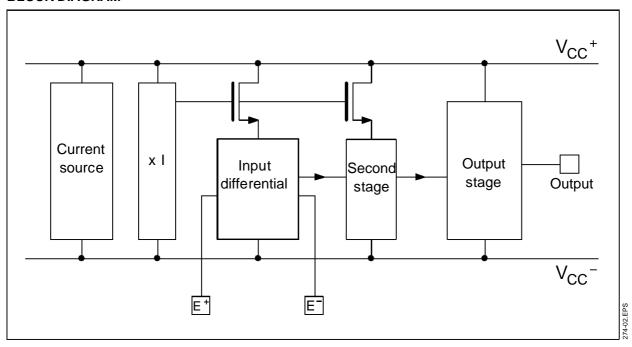
These CMOS amplifiers offer very high input impedance and extremely low input currents. The major advantage versus JFET devices is the very low input currents drift with temperature (see figure 2).

PIN CONNECTIONS (top view)



October 1995 1/8

BLOCK DIAGRAM



MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC} ⁺	Supply Voltage - (note 1)		18	V
V_{id}	Differential Input Voltage - (note 2)		±18	V
Vi	Input Voltage - (note 3)		-0.3 to 18	V
Ιο	Output Current for V _{CC} ⁺ ≥ 15V		±30	mA
I_{in}	Input Current		±5	mA
T _{oper}	Operating Free-Air Temperature Range	TS274C/AC/BC TS274I/AI/BI TS274M/AM/BM	0 to +70 -40 to +125 -55 to +125	°C
T _{stg}	Storage Temperature Range		-65 to +150	°C

Notes: 1. All voltage values, except differential voltage, are with respect to network ground terminal.

2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.

3. The magnitude of the input and the output voltages must never exceed the magnitude of the positive supply voltage.

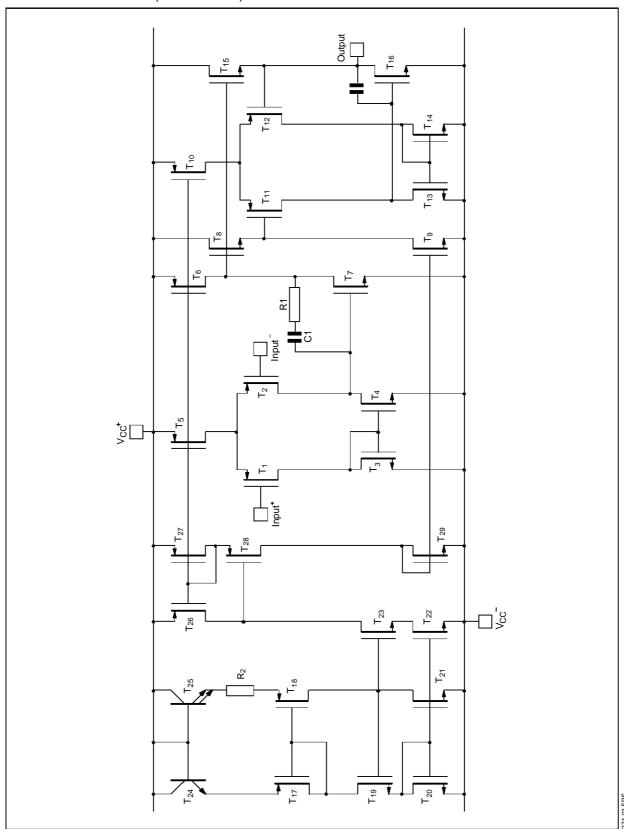
OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC} ⁺	Supply Voltage	3 * to 16	V
V _{icm}	Common Mode Input Voltage Range	0 to V _{CC} ⁺ - 1.5	V

* Selected devices only.



SCHEMATIC DIAGRAM (for 1/4 TS274)



ELECTRICAL CHARACTERISTICS

 $V_{CC}^+ = +10V$, $V_{CC}^- = 0V$, $V_{amb} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS274C/AC/BC			TS274I/AI/BI TS274M/AM/BM			Unit
		Min.	Тур.	Max.	Min.	Тур.	Max.	
Vio	$\label{eq:local_control_control_control} \begin{split} & \text{Input Offset Voltage} \\ & V_O = 1.4 V, V_{ic} = 0 V TS274 C/I/M \\ & $		1.1 0.9 0.25	10 5 2 12 6.5 3		1.1 0.9 0.25	10 5 2 12 6.5 3.5	mV
DV_{io}	Input Offset Voltage Drift		2			2		μV/°C
l _{io}	$ \begin{array}{l} \text{Input Offset Current - (note 1)} \\ V_{ic} = 5V, V_o = 5V \\ T_{min.} \leq T_{amb} \leq T_{max.} \end{array} $		1	100		1	200	pA
l _{ib}	$ \begin{array}{l} \text{Input Bias Current - (note 1)} \\ V_{ic} = 5V, V_o = 5V \\ T_{min.} \leq T_{amb} \leq T_{max.} \end{array} $		1	150		1	300	pA
V _{OH}		8.2 8.1	8.4		8.2 8	8.4		V
V _{OL}	High Level Output Voltage V _{id} = -100mV			50			50	mV
A _{vd}		10 7	15		10 6	15		V/mV
GBP	Gain Bandwidth Product $A_V = 40 dB$, $R_L = 10 k\Omega$, $C_L = 100 pF$ $f_{in} = 100 kHz$		3.5			3.5		MHz
CMR	Common Mode Rejection Ratio $V_0 = 1.4V$, $V_{ic} = 1V$ to 7.4V	65	80		65	80		dB
SVR	Supply Voltage Rejection Ratio $V_{CC}^{\dagger} = 5V$ to 10V , $V_0 = 1.4V$	60	70		60	70		dB
Icc	Supply Current (per amplifier) $A_V = 1, \text{ no load, } V_0 = 5V$ $T_{min.} \le T_{amb} \le T_{max.}$		1000	1500 1600		1000	1500 1700	μА
lo	Output Short Circuit Current V _{id} = 100mV, V _o = 0V		60			60		mA
I _{sink}	Output Sink Current $V_{id} = -100$ mV, $V_0 = V_{CC}$		45			45		mA
SR	Slew-Rate at Unity Gain $R_L = 10k\Omega$, $C_L = 100pF$, $V_i = 3 to 7V$		5.5			5.5		V/μs
Øm	Phase Margin at Unity Gain $A_V = 40 dB$, $R_L = 10 k\Omega$, $C_L = 100 pF$		40			40		Degrees
Kov	Overshoot Factor		30			30		%
en	Equivalent Input Noise Voltage $f = 1kHz$, $R_S = 100\Omega$		30			30		<u>nV</u> √Hz
V _{O1} /V _{O2}	Channel Separation		120			120		√Hz dB

Note: 1. Maximum values including unavoidable inaccuracies of the industrial test.

274-05.EPS

274-07.EPS

TYPICAL CHARACTERISTICS

Figure 1: Supply Current (each amplifier) versus Supply Voltage

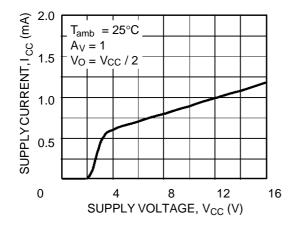


Figure 3a: High Level Output Voltage versus High Level Output Current

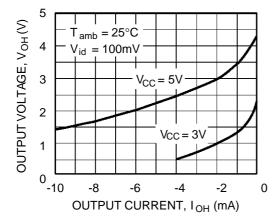


Figure 4a: High Level Output Voltage versus High Level Output Current

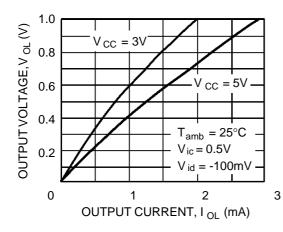


Figure 2: Input Bias Current versus Free Air Temperature

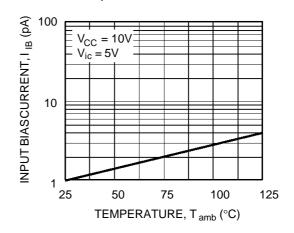


Figure 3b : High Level Output Voltage versus HIgh Level Output Current

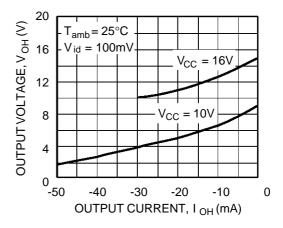
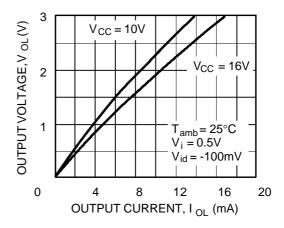


Figure 4b : High Level Output Voltage versus High Level Output Current



274-08.EPS

274-04.EPS

274-06.EPS

TYPICAL CHARACTERISTICS (continued)

Figure 5 : Open Loop Frequency Response and Phase Shift

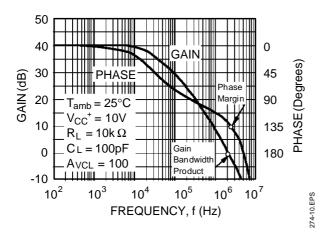


Figure 7: Phase Margin versus Supply Voltage

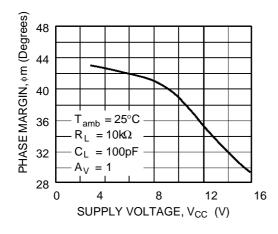


Figure 9: Slew Rates versus Supply Voltage

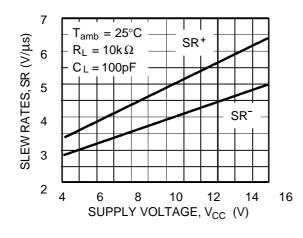


Figure 6 : Gain Bandwidth Product versus Supply Voltage

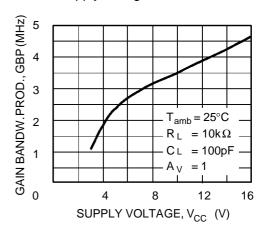


Figure 8: Phase Margin versus Capacitive Load

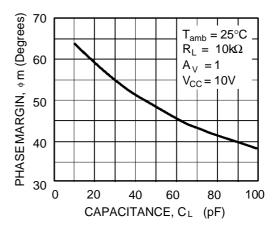
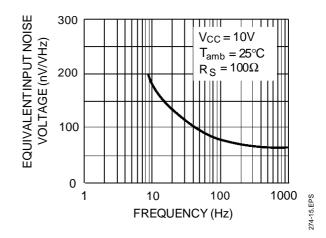


Figure 10: Input Voltage Noise versus Frequency

274-13.EPS

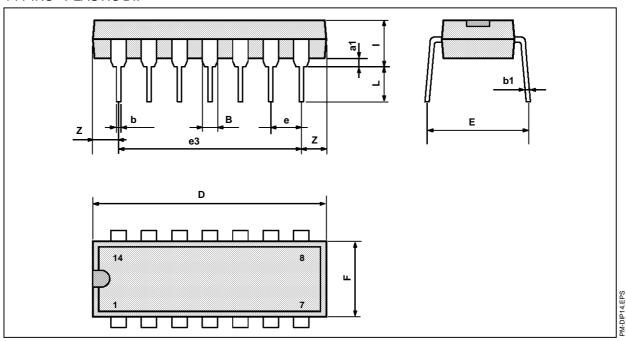


6/8

274-12.EPS

PACKAGE MECHANICAL DATA

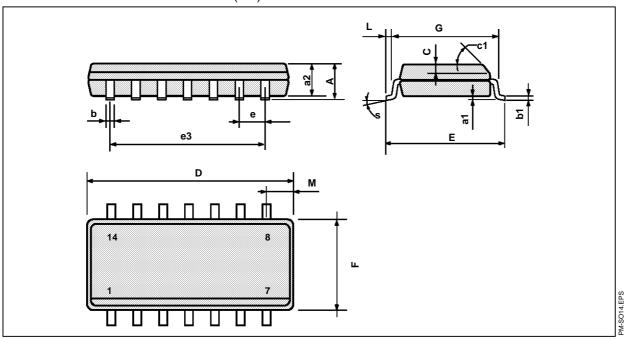
14 PINS - PLASTIC DIP



Dimensions		Millimeters			Inches	
Dillielisions	Min.	Тур.	Max.	Min.	Тур.	Max.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
i			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

PACKAGE MECHANICAL DATA

14 PINS - PLASTIC MICROPACKAGE (SO)



Dimensions	-	Millimeters			Inches	-
Difficusions	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
a1	0.1		0.2	0.004		0.008
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.020	
c1			45°	(typ.)		
D	8.55		8.75	0.336		0.334
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.150		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.020		0.050
М			0.68			0.027
S	8° (max.)					

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No licence is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1995 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.